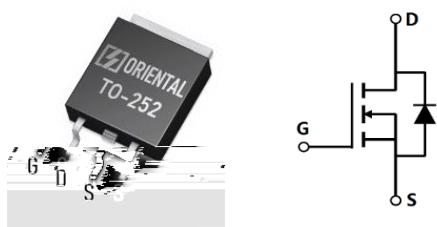


Parameter	Value	Unit
$V_{DS, \min} @ T_{j(\max)}$	60	V
$I_D, \text{pulse}$	204	A
$R_{DS(ON), \max} @ V_{GS}=10V$	10	
$Q_g$	17.9	nC

Product Name	Package	Marking
SFS06R10DF	TO252	SFS06R10D



**Absolute Maximum Ratings** at  $T_j=25^\circ\text{C}$  unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	$V_{DS}$	60	V
Gate-source voltage	$V_{GS}$	$\pm 20$	V
Continuous drain current <sup>1)</sup> , $T_C=25^\circ\text{C}$	$I_D$	68	A
Pulsed drain current <sup>2)</sup> , $T_C=25^\circ\text{C}$	$I_{D, \text{pulse}}$	204	A

 Continuous diode forward current<sup>1)</sup>,  $T_C=25^\circ\text{C}$ 


1-



### Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C <sub>iss</sub>		1204		pF	V <sub>GS</sub> =0 V, V <sub>DS</sub> =50 V, 0 / Hz
Output capacitance	C <sub>oss</sub>		194		pF	
Reverse transfer capacitance	C <sub>rss</sub>		9.9		pF	
Turn-on delay time	t <sub>d(on)</sub>		23.9		ns	V <sub>GS</sub> =10 V, V <sub>DS</sub> =50 V, R <sub>G</sub> 1 I <sub>D</sub> =25 A
Rise time	t <sub>r</sub>		4.6		ns	
Turn-off delay time	t <sub>d(off)</sub>		37.8		ns	
Fall time	t <sub>f</sub>		6.4		ns	

### Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q <sub>g</sub>		17.9		nC	V <sub>GS</sub> =10 V, V <sub>DS</sub> =50 V, I <sub>D</sub> =25 A
Gate-source charge	Q <sub>gs</sub>		3.8		nC	
Gate-drain charge	Q <sub>gd</sub>		4.2		nC	
Gate plateau voltage	V <sub>plateau</sub>		4.2		V	

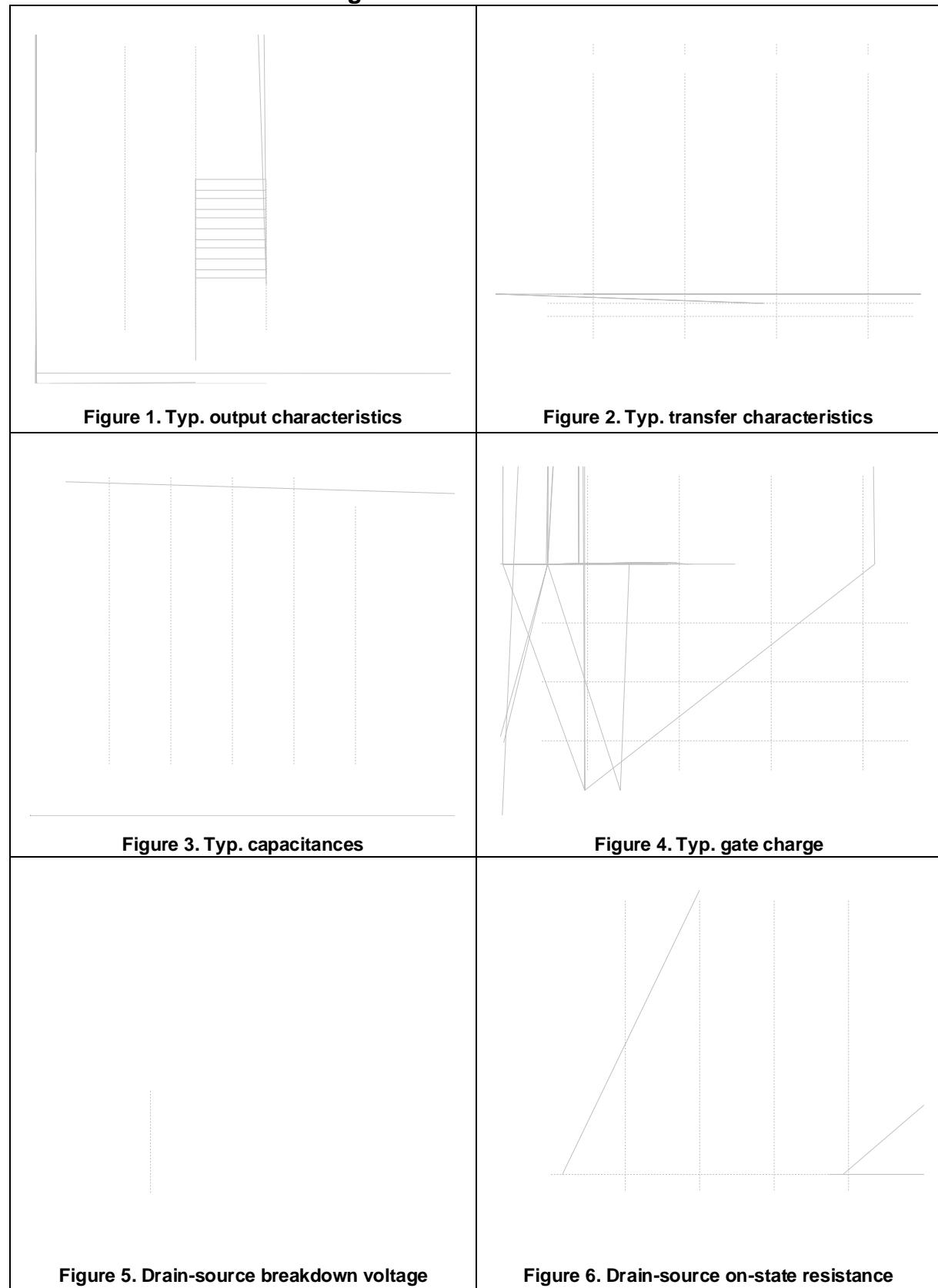
### Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V <sub>SD</sub>			1.3	V	I <sub>S</sub> =20 A, V <sub>GS</sub> =0 V
Reverse recovery time	t <sub>rr</sub>		42.6		ns	V <sub>R</sub> =50 V, I <sub>S</sub> =25 A, 0 / .
Reverse recovery charge	Q <sub>rr</sub>		36.3		nC	
Peak reverse recovery current	I <sub>rrm</sub>		1.4		A	

### Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) Pd is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of R<sub>G</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T<sub>a</sub>=25 °C.
- 5) V<sub>DD</sub>=30 V, V<sub>GS</sub>=10 V, L=0.3 mH, starting T<sub>j</sub>=25 °C.

### Electrical Characteristics Diagrams



**SFS06R10DF**

Enhancement Mode N-Channel Power MOSFET

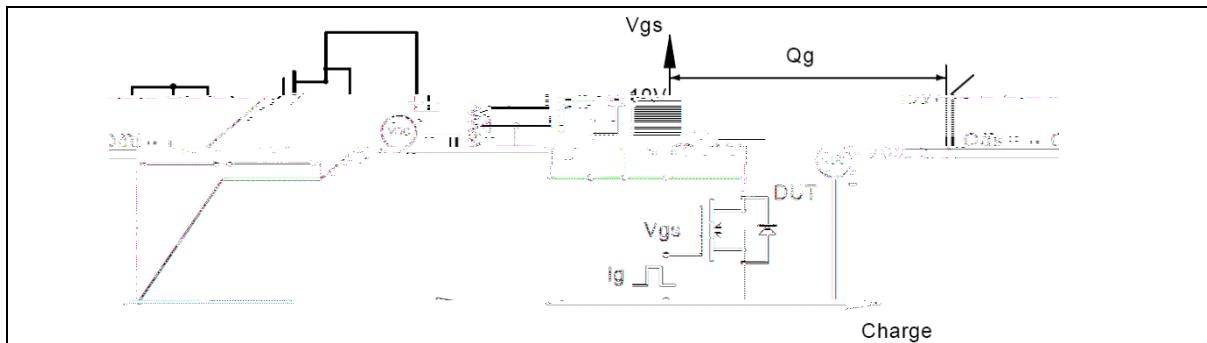


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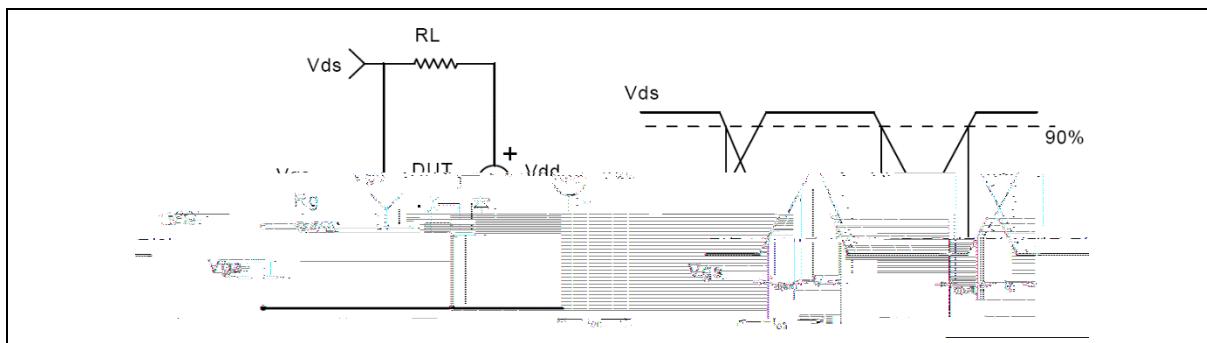
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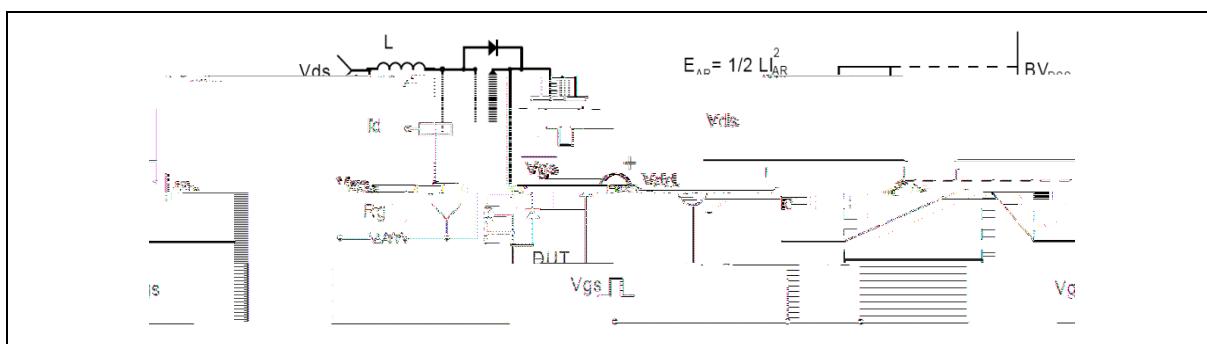
### Test circuits and waveforms



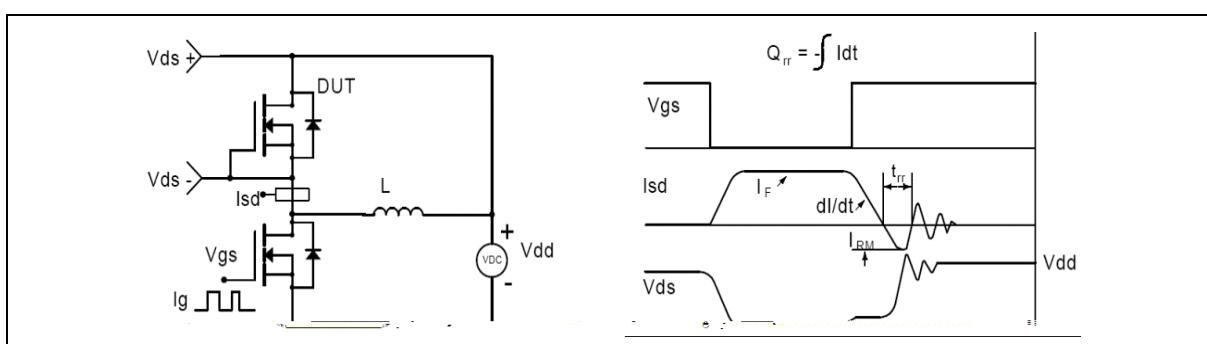
**Figure 1. Gate charge test circuit & waveform**



**Figure 2. Switching time test circuit & waveform**

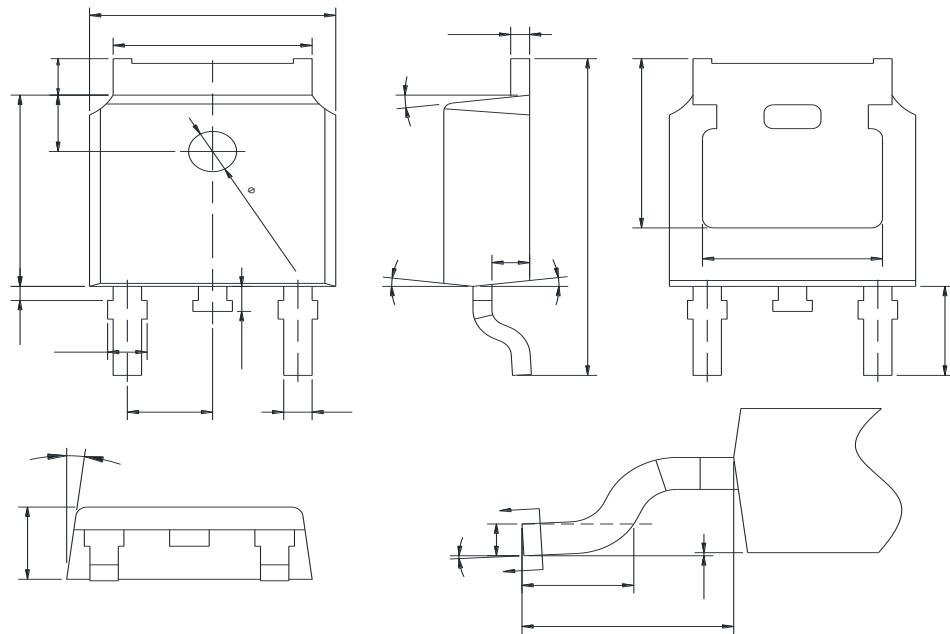


**Figure 3. Unclamped inductive switching (UIS) test circuit & waveform**



**Figure 4. Diode reverse recovery test circuit & waveform**

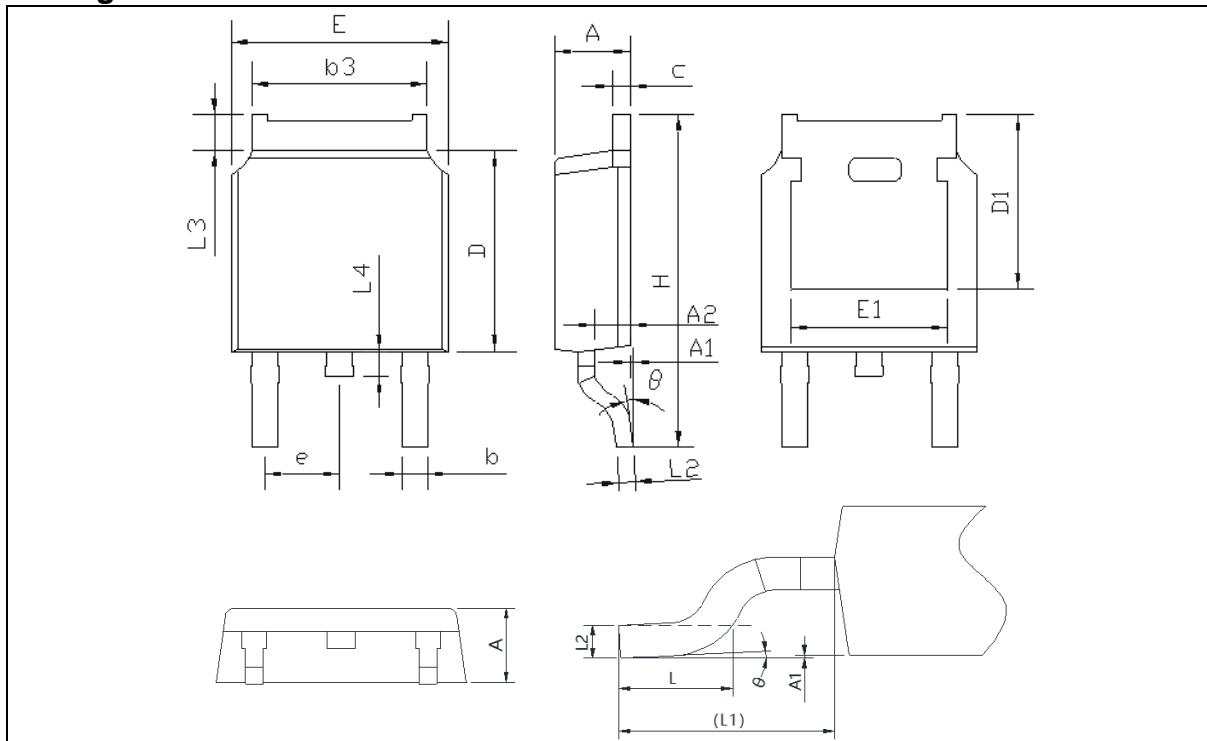
## Package Information



Symbol	mm		
	Min	Nom	Max
A	2.20	2.30	2.38
A1	0.00	-	0.10
A2	0.90	1.01	1.10
b	0.72	-	0.85
b1	0.71	0.76	0.81
b2	0.72	-	0.90
b3	5.13	5.33	5.46
c	0.47	-	0.60
c1	0.46	0.51	0.56
c2	0.47	-	0.60
D	6.00	6.10	6.20
D1	5.25	-	-
E	6.50	6.60	6.70
E1	4.70	-	-
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.508 BSC		
L3	0.90	-	1.25
L4	0.60	0.80	1.00
L5	0.15	-	0.75
L6	1.80 REF		
0	0	-	
1			

Version 1: TO252-J package outline dimension

### Package Information



Symbol	mm		
	Min	Nom	Max
A	2.20	2.30	2.38
A1	0.00	-	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30 REF		
E	6.40	6.60	6.73
E1	4.63	-	-
e	2.286 BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90 REF		
L2	0.51 BSC		
L3	0.88	-	1.28
L4	0.50	-	1.00
	0	-	

Version 2: TO252-P package outline dimension

## Ordering Information

Package Type	Units/ Reel	Reels/ Inner Box	Units/ Inner Box
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